Part Number	Customer

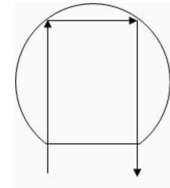
Category		**Parameter**	**Specification**	**Measurement Method**
OverallWafer	1.0	Diameter	150.00 +/- 0.50 mm	Wafer Vendor
	2.0	Primary Flat Length	57.50 +/- 2.50 mm	Wafer Vendor
	3.0	Primary Flat Orientation	{110} +/- 0.5 degree	Wafer Vendor
	4.0	Secondary Flat Length	None	Wafer Vendor
	5.0	Overall Thickness	400.00 +/- 6.00 µm	ADE, 100%
	6.0	Total Thickness Variation (TTV)	<3.00µm	Guaranteed by Process
	7.0	Bow	<60.00µm	ADE 100%, SEMI MF1530.
	8.0	Warp	<60.00µm	ADE 100%, SEMI MF1530.
	9.0	Edge Chips	none	Bright Light, 100%
	10.0	Edge Exclusion	5mm	
	11.0	Wafer outer edge profile	Rounded edge	Microscope image, 1 wfr/Box
HandleSilicon	12.0	Handle Growth Method	CZ	Wafer Vendor
	13.0	Handle Orientation	{100} +/-0.5 degree	Wafer Vendor
	14.0	Handle Thickness	395.00 +/- 5.00 µm	ADE, 100%
	15.0	Handle Doping Type	N	Wafer Vendor
	16.0	Handle Dopant	Phosphorous	Wafer Vendor
	17.0	Handle Resistivity	1~10 Ohm-cm	Wafer Vendor
	18.0	Backside Finish	Polished with oxide, laser mark, and light handling marks	Guaranteed by process
BuriedOxide	19.0	Oxide Type	Thermal	
	20.0	Oxide Thickness	10,000.00 +/- 500.00 A	Nanospec centre point, 4%
	21.0	Oxide formed on	Handle and/or Device Wafer	
DeviceSilicon	22.0	Device Orientation	{100} +/- 0.5 degree	Wafer Vendor
	23.0	Nominal Thickness	4.00 +/- 0.50 µm	ADE single point, 100%
	24.0	Distance to device silicon edge from wafer edge	<= 1.5mm	Typical by Process
	25.0	Edge Removal Angle	45.00 +/- 15.00 deg	Graranteed by process
	26.0	Edge Removal Depth in Handle	<100um	Graranteed by process
	27.0	Device Doping Type	N	Wafer Vendor
	28.0	Device Dopant	Phosphorous	Wafer Vendor
	29.0	Device Growth Method	CZ	Wafer Vendor
	30.0	Device Resistivity	1~5 Ohm-cm	Wafer Vendor
	31.0	Voids	none	Bright Light, 100% (note 2)
	32.0	Scratches	none	Bright Light, 100% (note 2)
	33.0	Haze	none	Bright Light, 100% (note 2)
	34.0	Other Surface Defects	none	Bright Light, 100% (note2)

Part Number	Customer

Category	Parameter	Specification	Measurement Method
Shipping Details	Wafer per box :	Max 25	
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 150.00mm Antistatic Double Bagging	
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness	

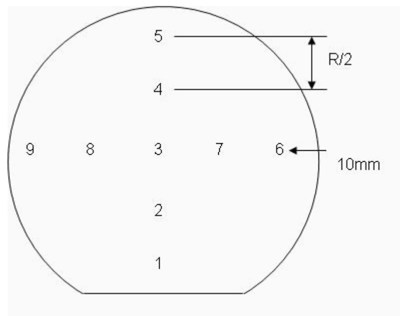
Explanatory Notes

1. Microscope inspection performed using microscope scan as below. 5x objective.



2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information